Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

2SK2750

Chopper Regulator, DC-DC Converter and Motor Drive Applications

 $\begin{array}{ll} \bullet & Low\ drain-source\ ON\ resistance & : R_{DS}\ (ON) = 1.7\ \Omega\ (typ.) \\ \bullet & High\ forward\ transfer\ admittance & : |Y_{fs}| = 3.0\ S\ (typ.) \\ \bullet & Low\ leakage\ current & : I_{DSS} = 100\ \mu A\ (max)\ (V_{DS} = 600\ V) \\ \bullet & Enhancement-mode & : V_{th} = 2.0 \sim 4.0\ V\ (V_{DS} = 10\ V,\ I_{D} = 1\ mA) \\ \end{array}$

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	600	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	600	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	I _D	3.5	Α	
	Pulse (Note 1)	I _{DP}	14	Α	
Drain power dissipation (Tc = 25°C)		P _D	35	W	
Single pulse avalanche energy (Note 2)		E _{AS}	201	mJ	
Avalanche current		I _{AR}	3.5	Α	
Repetitive avalanche energy (Note 3)		E _{AR}	3.5	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Weight: 1.9 g (typ.)

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	3.57	°C / W
Thermal resistance, channel to ambient	R _{th (ch-a)}	62.5	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

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Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 28.8 mH, R_G = 25 Ω , I_{AR} = 3.5 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

Please handle with caution.

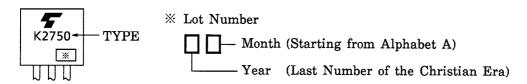
Electrical Characteristics (Ta = 25°C)

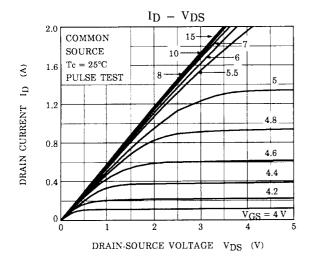
Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I _{GSS}	V _{GS} = ±25 V, V _{DS} = 0 V	_	_	±10	μΑ
Gate-source bre	eakdown voltage	V (BR) GSS	$I_{G} = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$	±30	_	_	V
Drain cut-off cur	rent	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	100	μΑ
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	600	_	_	V
Gate threshold v	roltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source Ol	N resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 1.8 A	_	1.7	2.2	Ω
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 1.8 A	2.0	3.0	_	S
Input capacitano	е	C _{iss}		_	800	_	
Reverse transfer	capacitance	C _{rss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	_	6	_	pF
Output capacitar	Output capacitance C _{oss}		_	65	_]	
Switching time	Rise time	t _r	V_{GS} $0V$ $R_{L}=111\Omega$ $V_{DD}=200V$	_	15	_	- ns
	Turn-on time	t _{on}		_	50	_	
	Fall time	t _f		_	15	_	
	Turn-off time	t _{off}	Duty $\leq 1\%$, $t_{\mathbf{w}} = 10 \mu \text{s}$	_	85		
Total gate charg plus gate-drain)		Qg		_	20	_	_
Gate-source charge Q_{gs} $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3.5 \text{ A}$			10		nC		
Gate-drain ("mil	ler") Charge	Q _{gd}			10	_	

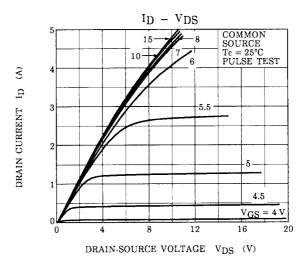
Source-Drain Ratings and Characteristics (Ta = 25°C)

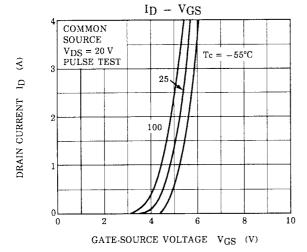
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	1	_	3	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	14	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 3.5 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 3.5 A, V _{GS} = 0 V		1400	_	ns
Reverse recovery charge	Q _{rr}	dl _{DR} / dt = 100 Å / μs		9	-	μC

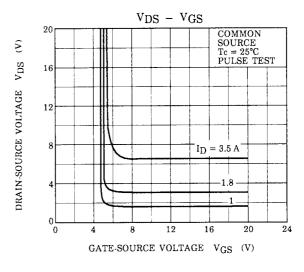
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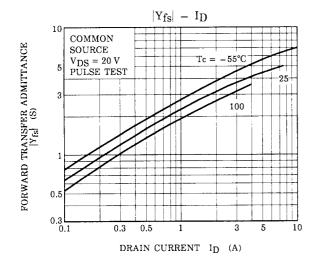


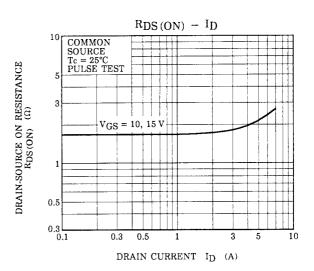




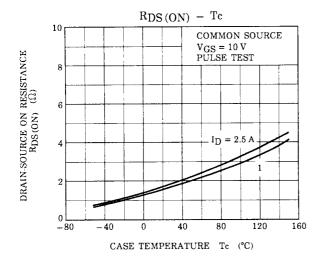


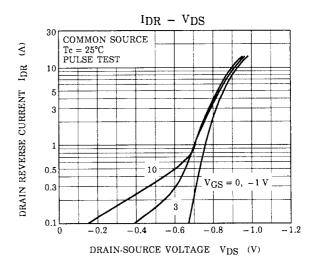


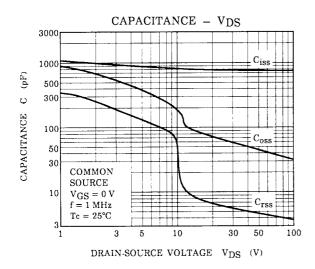


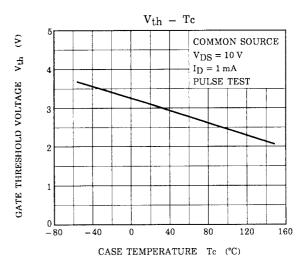


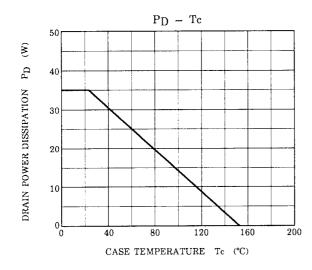
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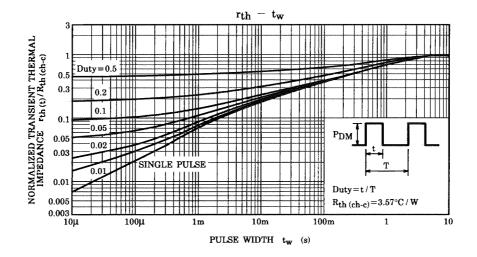


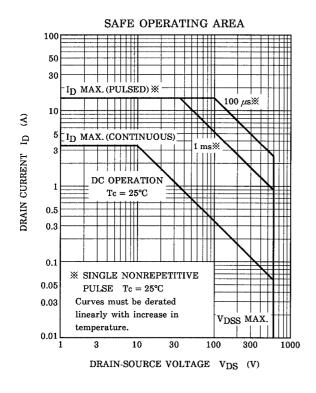


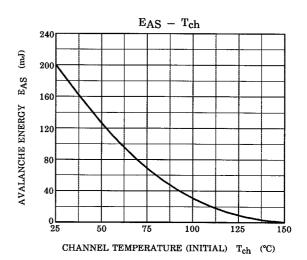


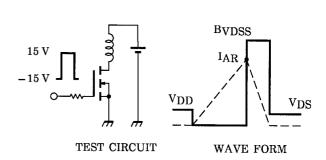


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$$\begin{aligned} R_G &= 25 \ \Omega \\ V_{DD} &= 90 \ V, \ L = 28.8 \ mH \end{aligned} \qquad E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - VDD} \right)$$

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